



Figure 2 (a), (b), and (c) Side wall coverage of low-deposition-rate SiO₂ film, deposited using Unaxis ICP tool at 100 °C, with chamber pressure=5 mT, bias/ICP powers=15 (28 V)/800 W, 100%SiH₄/O₂/Ar=7.5/15/20 sccm, and deposition time=294 s.